



## COAXIAL SOLID STATE

# High Power Amplifier RFE-24M30M075X+

Mini-Circuits

50Ω 4X 19W 27 MHz 1 SMA Input / 4 SMA Output

### THE BIG DEAL

- One input, four 19W outputs
- 27 MHz ISM band
- Suitable for CW and pulsed signals
- High gain, 16 dB typical at  $P_{3dB}$
- 55% typical efficiency
- Integrated harmonic suppression
- Temperature compensated gate bias

### APPLICATIONS

- Industrial heating
- Materials processing
- Food processing (heating, tempering, and pasteurization)
- Microwave-assisted chemistry
- Plasma generation
- Plasma surface treatment
- Disinfection
- Chemistry
- RF-excited lasers
- Medical (heating, hyperthermia, and ablation)
- Semiconductor RF generators

### PRODUCT OVERVIEW

The RFE-24M30M075X+ is a new generation light weight solid state connectorized power amplifier module. One input signal generates four equal output signals with a typical  $P_{3dB}$  of 19W each. The amplifier is intended as a driver for high power 27 MHz amplifiers, such as the RFE-24M30M1K7X+. The RFE-24M30M075X+ can be used in a wide range of industrial, scientific and medical applications in the 27 MHz ISM band. The amplifier uses state-of-the-art high ruggedness semiconductor technology. The amplifier is capable of amplifying CW and pulsed signals. A temperature compensated gate bias circuit is provided. Mounting holes for an M3 screw are provided to mount the amplifier to a heatsink or cooling plate in larger systems. Easy screw-on power supply connections are provided outside the shield.

### KEY FEATURES

Feature	Advantages
75W CW Power	Four equal channels with 19W output power ( $P_{3dB}$ ) for a wide range of industrial, scientific and medical applications in the 27 MHz ISM band. Designed to drive four RFE-24M30M1K7X+ amplifiers to create a generator with output power >5kW.
High Gain	With only 0.5W of input power and a typical gain of 16 dB at $P_{3dB}$ , only two amplifier stages are needed to generate 5kW.
Harmonic Filtering	Harmonic filtering inside this power amplifier ensures that the final stages receive a clean drive signal.
Temperature Compensated Gate Bias	A temperature compensated gate bias circuit is integrated in the PA.
Easy interfacing	Power supply connections are easily accessible outside the shield.
Small and lightweight	The compact amplifier design (202mm x 118mm x 28mm) is lightweight (608 g) which makes it suitable for integration in high power systems that require multiple amplifiers.
Cooling	The power amplifier can easily be mounted on a heatsink using the provided M3 mounting holes.
Low voltage	The RFE-24M30M075X+ operates over a large 50-66V supply voltage range.



Generic photo used for illustration purposes only

Model No.	RFE-24M30M075X+
Case Style	VU3196
Connectors	1 SMA INPUT / 4 SMA OUTPUT

**+RoHS Compliant**  
The +Suffix identifies RoHS Compliance.  
See our website for methodologies and qualifications





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### ELECTRICAL SPECIFICATIONS PER CHANNEL AT T<sub>Mounting Base</sub> = +25°C, V<sub>DS</sub> = 65V, 50Ω SYSTEM

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Frequency Range	f			27.12		MHz
Operating Voltage	V <sub>DS</sub>	27.12 MHz	50	65	66	V
Input Power	P <sub>IN</sub>	27.12 MHz	-	0.5	1.25	Watts
			-	27	31	dBm
Output Power at 1dB compression	P <sub>1dB</sub>	27.12 MHz	12	-	-	Watts
			40.8	-	-	dBm
Output Power at 3dB compression	P <sub>3dB</sub>	27.12 MHz	13.5	-	-	Watts
			41.3	-	-	dBm
Power Gain	G <sub>p</sub>	P <sub>3dB</sub> at 27.12MHz	13	-	-	dB
Efficiency	η	P <sub>3dB</sub> at 27.12MHz	48	-	-	%
Input VSWR		P <sub>3dB</sub> at 27.12MHz	-	-	1.92	:1
Harmonics (H2 and H3)		P <sub>3dB</sub> at 27.12MHz	-	-10	-	dBc

Test conditions: V<sub>DS</sub>=65V, I<sub>DQ</sub>=0.04A, f=27.12 MHz, T<sub>MB</sub>=25°C, unless otherwise noted  
 All power measurements are performed while using a Mini-Circuits NLP-30+ Low Pass Filter in front of the power sensors.

### MAXIMUM RATINGS<sup>1</sup>

Parameter	Ratings
Mounting Base Temperature <sup>2</sup>	0°C to +65°C
Storage Temperature	0°C to +85°C
DC Voltage	66V
Input RF Power (no damage) <sup>3</sup>	+31 dBm

- Specifications apply to CW signals only. Permanent damage may occur if any of these limits are exceeded.
- Mounting Base Temperature is the Temperature of the Aluminum Base Plate.
- CW of +31dBm for 5 minutes maximum





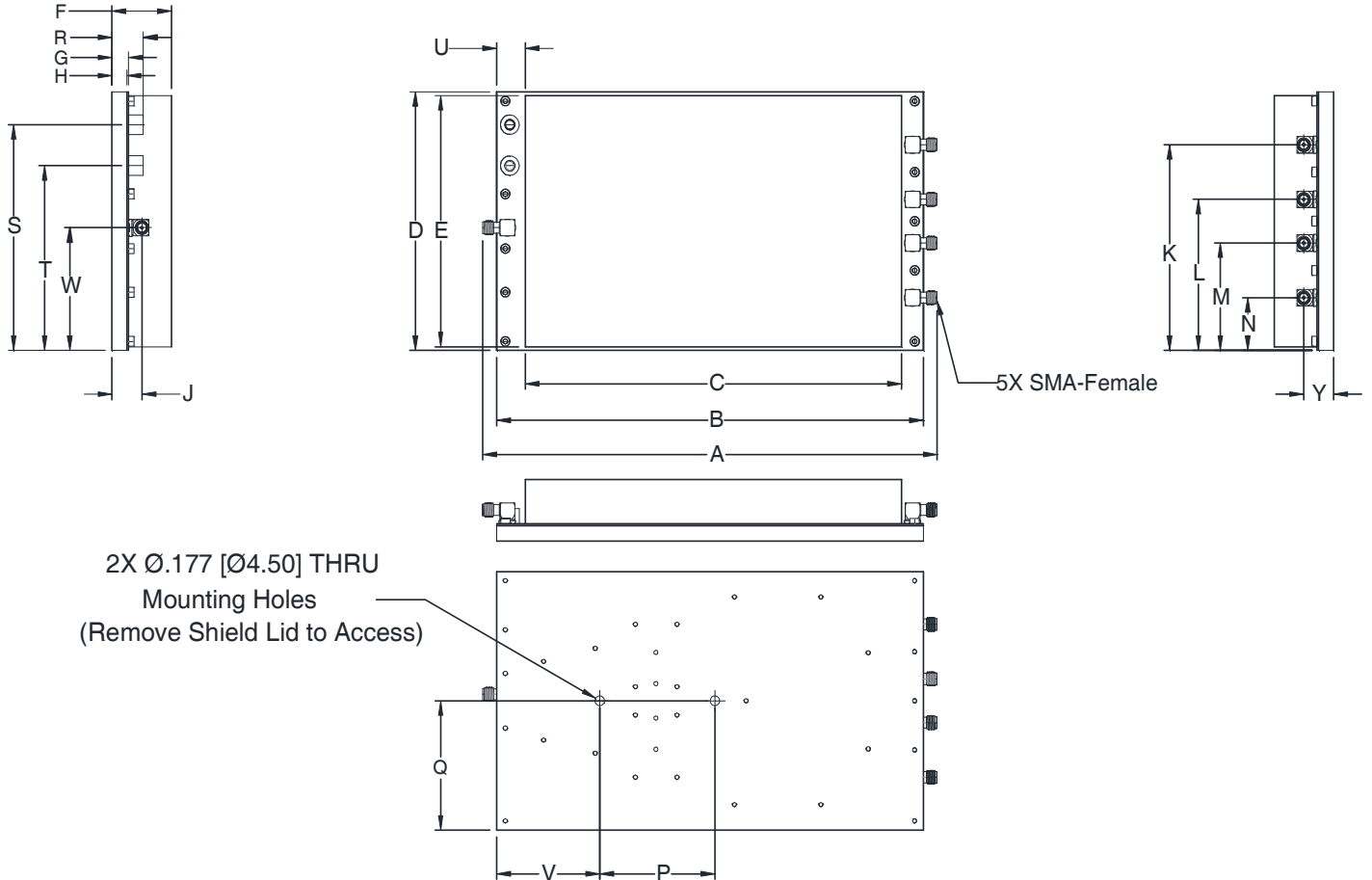
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## OUTLINE DRAWING



## OUTLINE DIMENSIONS (Inch/mm)

CASE #	A	B	C	D	E	F	G	H	J	K	L	M
VU3196	8.486 (215.54)	7.969 (202.40)	7.027 (178.49)	4.660 (118.36)	4.528 (115.00)	1.110 (28.19)	0.310 (7.87)	0.280 (7.11)	.560 (14.24)	3.708 (94.18)	2.724 (69.18)	1.936 (49.18)

CASE #	N	P	Q	R	S	T	U	V	W	Y	WEIGHT (GRAMS)
VU3196	.952 (24.18)	2.151 (54.63)	2.330 (59.18)	.586 (14.89)	4.070 (103.38)	3.330 (84.58)	.534 (13.56)	1.924 (48.87)	2.212 (56.18)	.560 (14.24)	608

Dimensions are in inches (mm). Tolerances: 2Pl. ±.01(0.254); 3Pl. ±.005(0.127)





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### TYPICAL ELECTRICAL PERFORMANCE PER CHANNEL OF RFE-24M30M075X+

Parameter	Typical Performance ( $T_{MB} = +25^{\circ}C$ )	Unit
Frequency	27	MHz
Supply Voltage	65	V
Total Input Power ( $P_{IN}$ )	27	dBm
CW Output Power ( $P_{OUT}$ @ $P_{IN}$ ) per Channel	42.8 19	dBm W
Efficiency (@19W per channel)	51.3	%
Gain (@19W per channel)	14.8	dB
Current	2.3	A

### AMPLIFIER INTERFACES

	<p>J3 +65V Supply Voltage Connector, M5 J4 Ground Connection, M5</p> <p>Tightening Torque 1.7 N-m (15 in-lbs) with max. of 2.15 N-m (19 in-lbs)</p> <p>Mating Hardware*: M5 screw equivalent to McMaster P/N 92095A308 Belville washer equivalent to McMaster P/N 90895A027 Ring Terminal equivalent to McMaster P/N 7113K29</p>
	<p>J1, J2, J6, J7, J8 - SMA Connector Receptacle, Female Socket 50Ohm</p>

\*Mating hardware not included with amplifier. Similar mating hardware available from other manufactures.



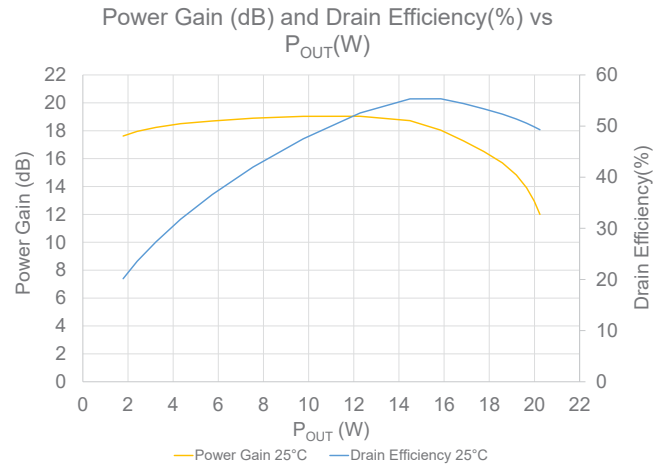
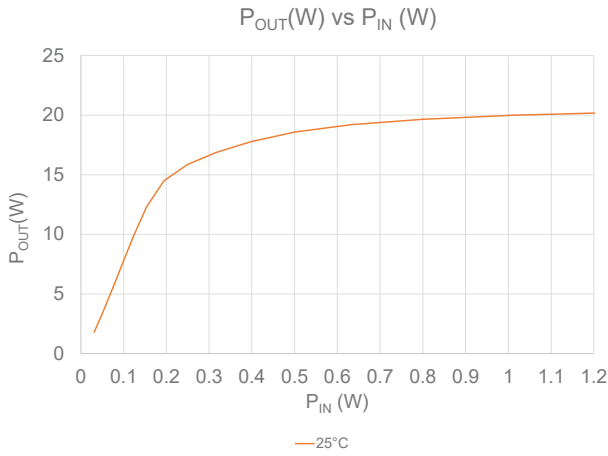
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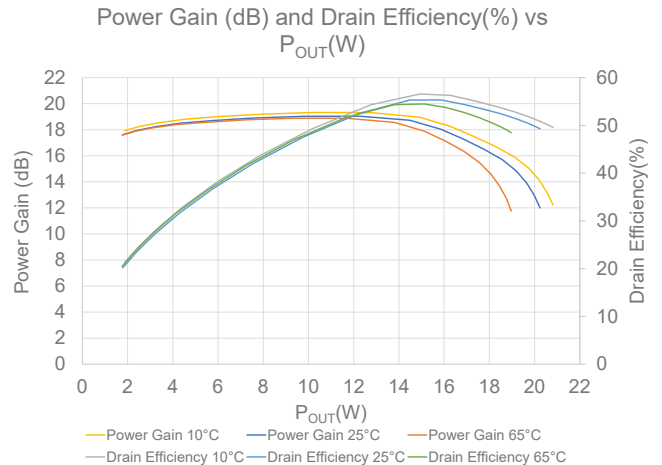
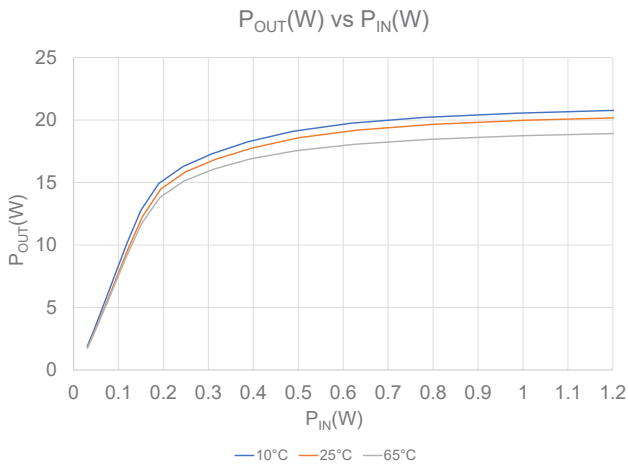
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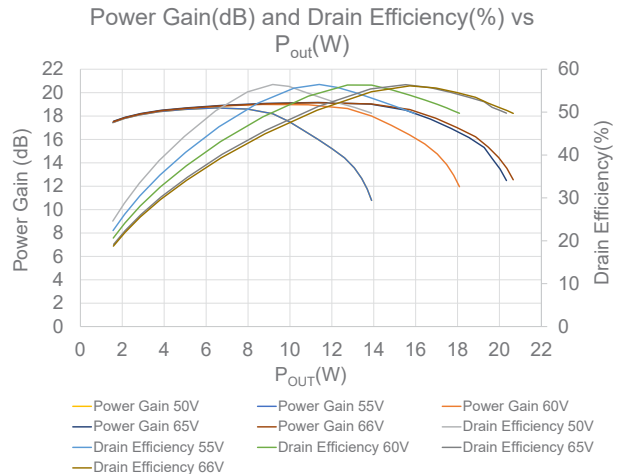
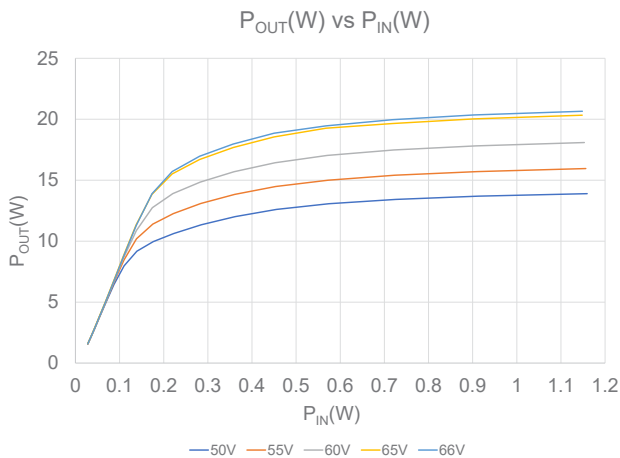
## TYPICAL PERFORMANCE DATA PER CHANNEL AT 27 MHZ ( $T_{MOUNTING\ BASE} = +25^{\circ}C, V_{DS} = 65V, 50\Omega\ SYSTEM$ )



## TYPICAL PERFORMANCE DATA PER CHANNEL AT 27 MHZ ACROSS DIFFERENT MOUNTING BASEPLATE TEMPERATURE ( $V_{DS} = 65V, 50\Omega\ SYSTEM$ )



## TYPICAL PERFORMANCE DATA PER CHANNEL ACROSS DIFFERENT VOLTAGE RANGE AT 27 MHZ ( $T_{MOUNTING\ BASE} = +25^{\circ}C, 50\Omega\ SYSTEM$ )





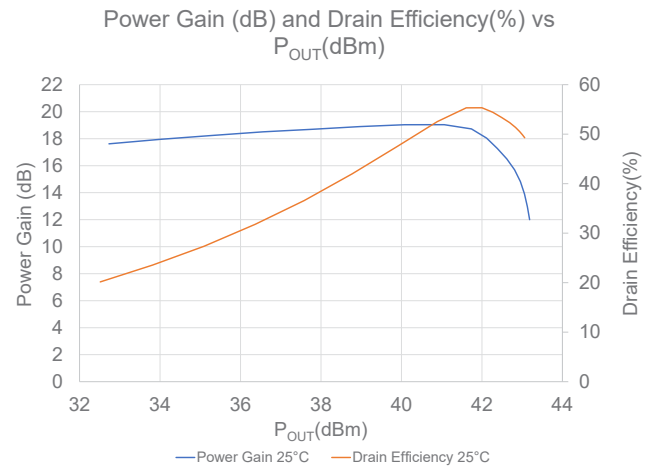
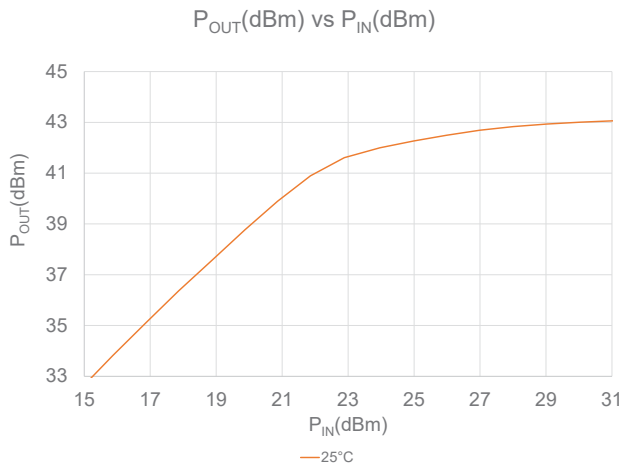
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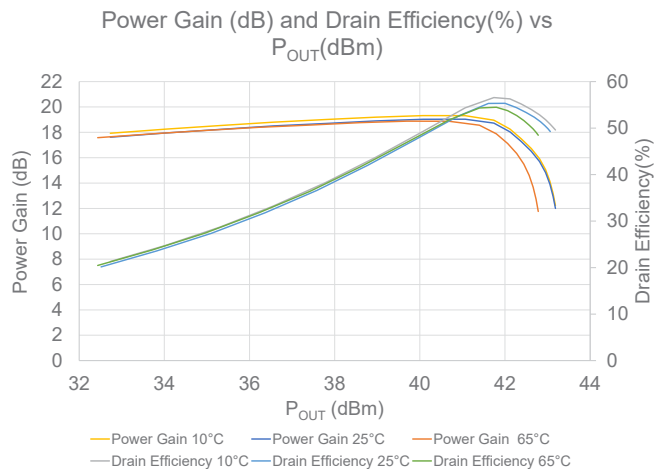
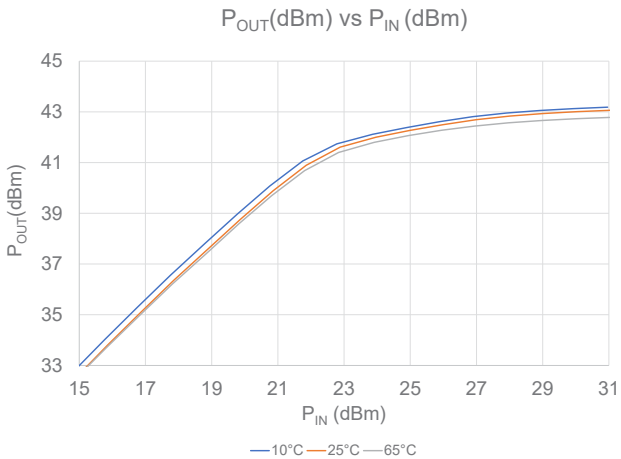
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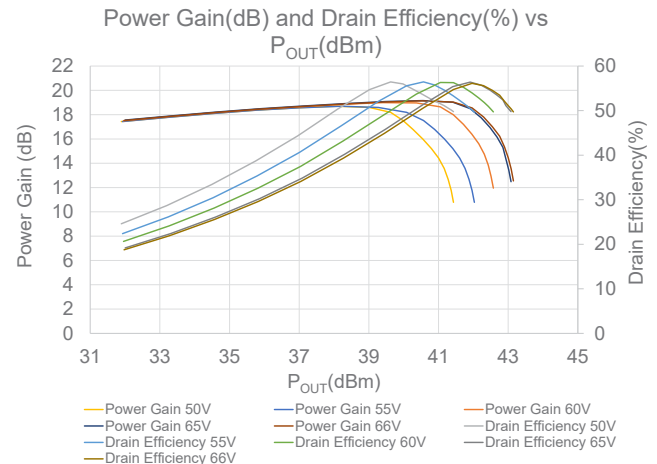
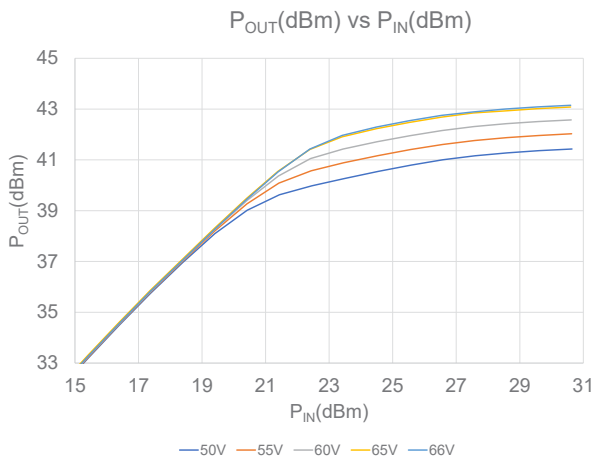
## TYPICAL PERFORMANCE DATA PER CHANNEL AT 27 MHz ( $T_{\text{MOUNTING BASE}} = +25^{\circ}\text{C}$ , $V_{\text{DS}} = 65\text{V}$ , 50Ω SYSTEM)



## TYPICAL PERFORMANCE DATA PER CHANNEL AT 27 MHz ACROSS DIFFERENT MOUNTING BASEPLATE TEMPERATURE ( $V_{\text{DS}} = 65\text{V}$ , 50Ω SYSTEM)



## TYPICAL PERFORMANCE DATA PER CHANNEL ACROSS DIFFERENT VOLTAGE RANGE AT 27 MHz ( $T_{\text{MOUNTING BASE}} = +25^{\circ}\text{C}$ , 50Ω SYSTEM)





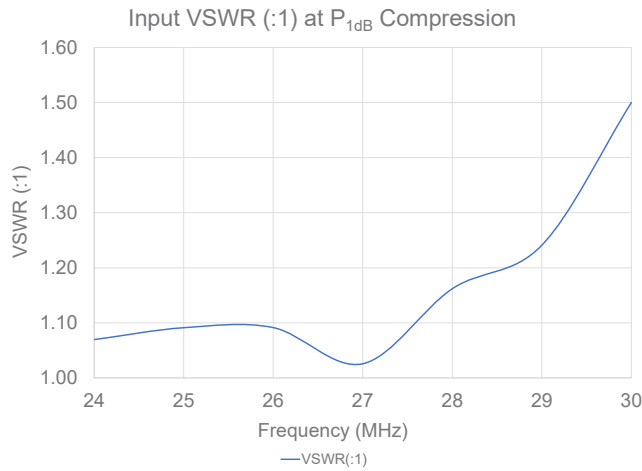
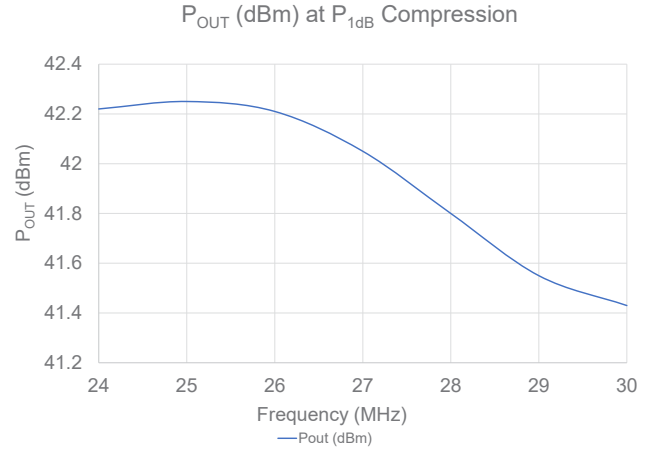
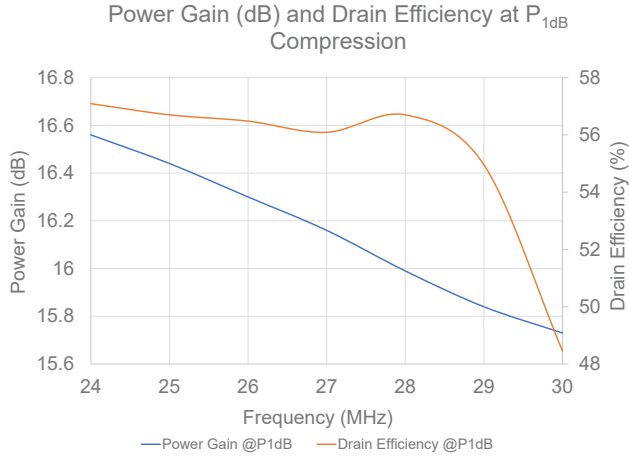
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## TYPICAL PERFORMANCE DATA PER CHANNEL ( $T_{\text{MOUNTING BASE}} = +25^{\circ}\text{C}$ , $V_{\text{DS}} = 65\text{V}$ , 50Ω SYSTEM)





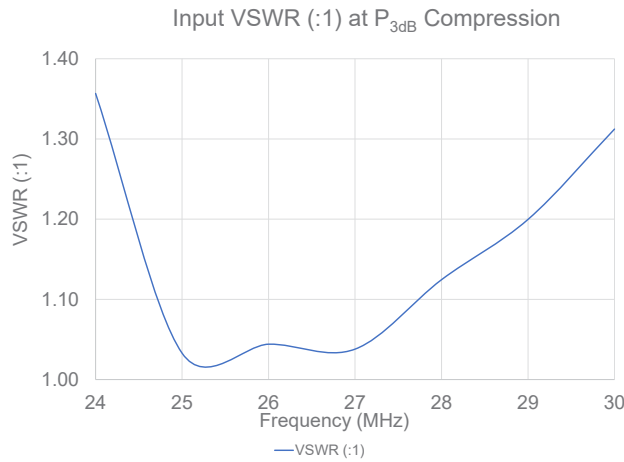
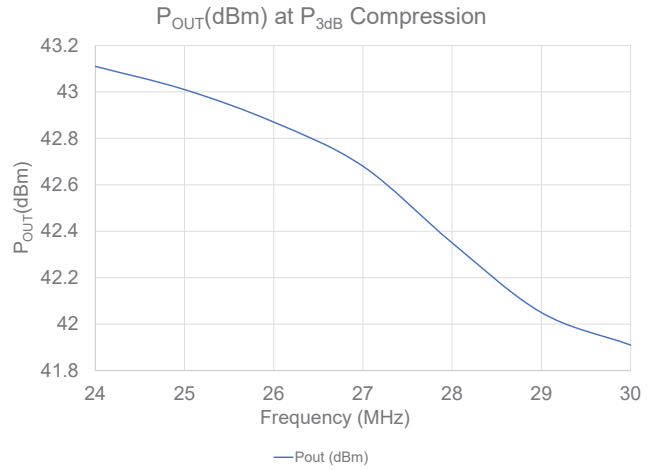
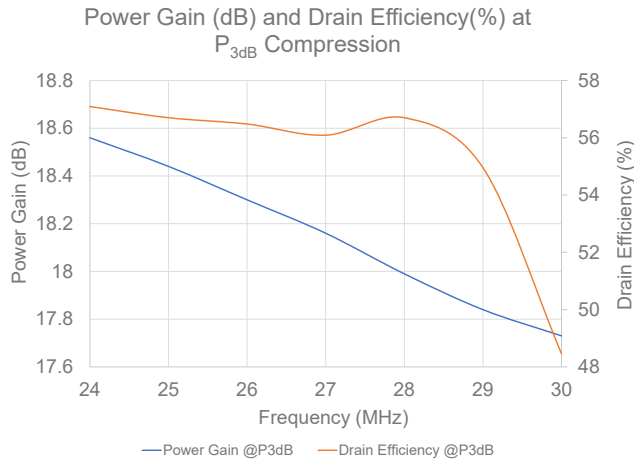
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### NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard. Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at [www.minicircuits.com/MCLStore/terms.jsp](http://www.minicircuits.com/MCLStore/terms.jsp)

